



安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

SD101AW-SD101CW

SOD-123 Schottky Barrier Rectifier Diode 肖特基势垒整流二极管

SOD-123



■ Features 特点

Fast switching time 快速开关时间
 Low forward voltage drop 低正向压降
 Surface mounted device 表面贴装器件
 Case 封装:SOD-123

■ Maximum Rating 最大额定值

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

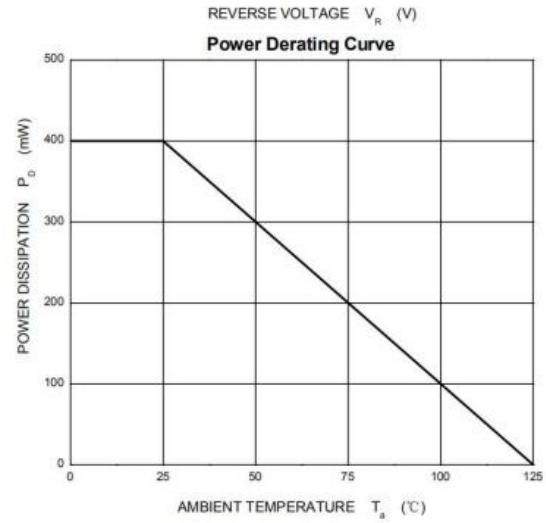
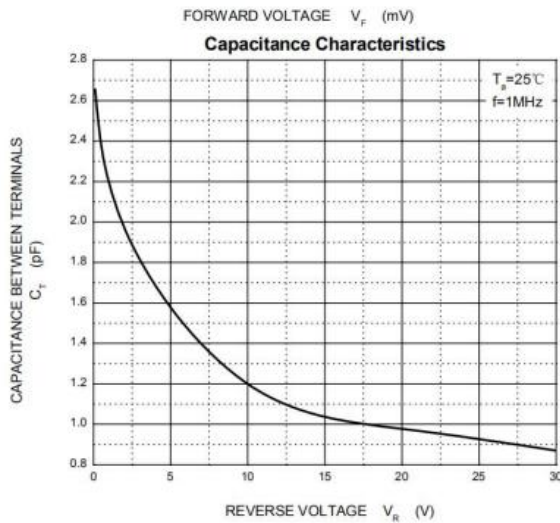
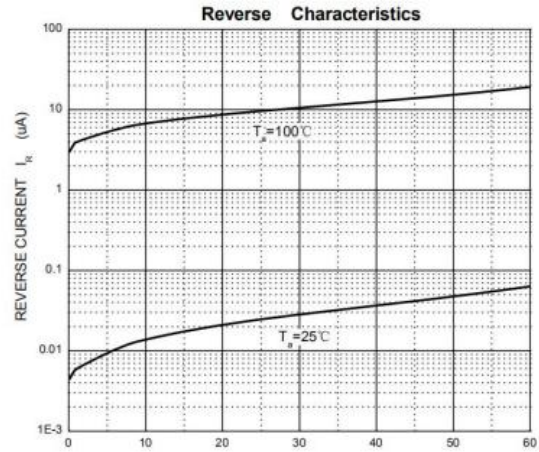
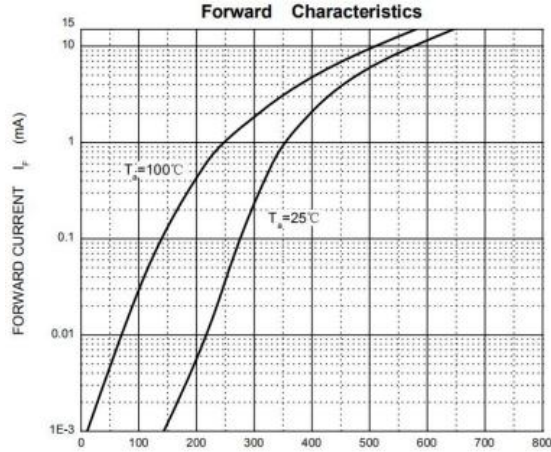
Characteristic 特性参数	Symbol 符号	SD101AW	SD101BW	SD101CW	Unit 单位
Device Marking 产品印字		S1	S2	S3	
Peak Reverse Voltage 反向峰值电压	V_{RRM}	60	50	40	V
DC Reverse Voltage 直流反向电压	V_R	60	50	40	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	42	35	28	V
Forward Rectified Current 正向整流电流	I_F	15			mA
Peak Surge Current 峰值浪涌电流	I_{FSM}	200			mA
Repetitive Peak Surge Current 重复峰值浪涌电流	I_{FRM}	50			mA
Power Dissipation 耗散功率	P_D	400			mW
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	250			$^{\circ}\text{C}/\text{W}$
Junction Temperature 结温	T_J	125			$^{\circ}\text{C}$
Storage Temperature 储藏温度	T_{stg}	-50to+150			$^{\circ}\text{C}$

■ Electrical Characteristics 电特性

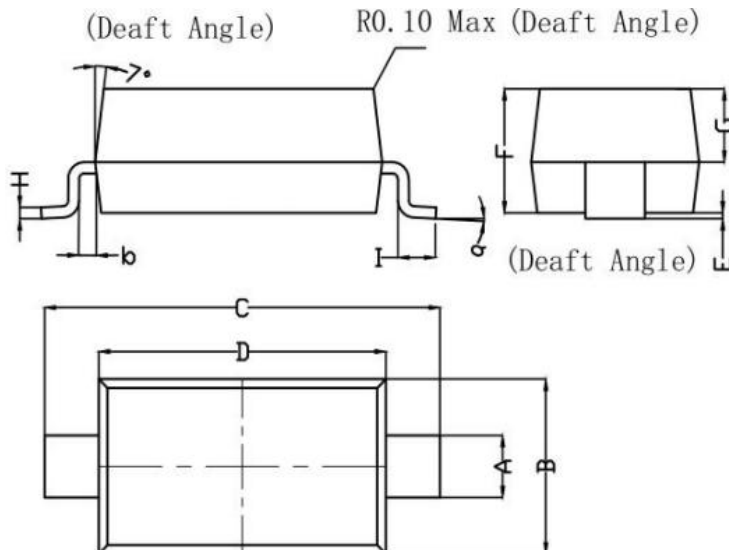
($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	SD101AW	SD101BW	SD101CW	Unit 单位	Condition 条件
Reverse Voltage 反向电压	V_R	60	50	40	V	$I_R=10\mu\text{A}$
Forward Voltage 正向电压	V_F	0.41 1	0.4 0.95	0.39 0.9	V	$I_F=1\text{mA}$ $I_F=15\text{mA}$
Reverse Current 反向电流	I_R	0.2			μA	$V_R=V_{RRM}$
Reverse Recovery Time 反向恢复时间	T_{rr}	1			nS	$I_F=I_R=5\text{mA}$ $I_{rr}=0.5\text{mA}$
Diode Capacitance 二极管电容	C_T	2			pF	$V_R=1\text{V}, f=1\text{MHz}$

Typical Characteristic Curve 典型特性曲线



Dimension 外形封装尺寸 SOD-123



Symbol	Dim in mm		
	Min	Nom	Max
A	0.520	0.550	0.570
B	1.400	1.550	1.700
C	3.350	3.650	3.850
D	2.550	2.650	2.850
E	0.000	0.050	0.100
F	1.050	1.100	1.150
G	0.620	0.650	0.670
H	0.100	0.110	0.120
I	0.250	0.350	0.450
a	0°	-	6°
b	0.4°	-	0.8°